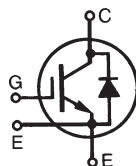


# 900V XPT™ IGBT GenX3™ w/ Diode

## IXYN80N90C3H1

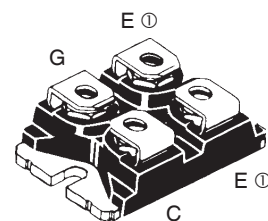
High-Speed IGBT  
for 20-50 kHz Switching



$$\begin{aligned} V_{CES} &= 900V \\ I_{C90} &= 70A \\ V_{CE(sat)} &\leq 2.7V \\ t_{fi(typ)} &= 86ns \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	900	V
$V_{CGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GE} = 1M\Omega$	900	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$	115	A
$I_{C90}$	$T_C = 90^\circ\text{C}$	70	A
$I_{F110}$	$T_C = 110^\circ\text{C}$	42	A
$I_{CM}$	$T_C = 25^\circ\text{C}$ , 1ms	340	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 150^\circ\text{C}$ , $R_G = 2\Omega$ Clamped Inductive Load	$I_{CM} = 160$ @ $V_{CE} \leq V_{CES}$	A
$P_C$	$T_C = 25^\circ\text{C}$	500	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$V_{ISOL}$	50/60Hz $t = 1\text{min}$ $I_{ISOL} \leq 1\text{mA}$ $t = 1\text{s}$	2500 3000	V~ V~
$M_d$	Mounting Torque Terminal Connection Torque	1.5/13 1.3/11.5	Nm/lb.in Nm/lb.in
<b>Weight</b>		30	g

SOT-227B, miniBLOC  
E153432



G = Gate, C = Collector, E = Emitter  
ⓐ either emitter terminal can be used as  
Main or Kelvin Emitter

### Features

- Optimized for Low Switching Losses
- Square RBSOA
- Isolation Voltage 2500V~
- Anti-Parallel Sonic Diode
- Positive Thermal Coefficient of  $V_{ce(sat)}$
- High Current Handling Capability
- International Standard Package

### Advantages

- High Power Density
- Low Gate Drive Requirement

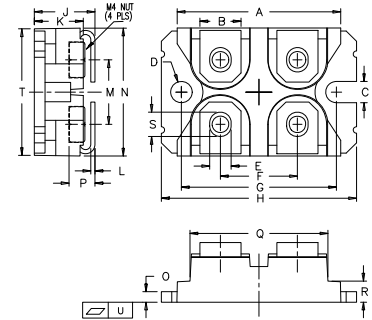
### Applications

- High Frequency Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu\text{A}$ , $V_{GE} = 0V$	950		V
$V_{GE(th)}$	$I_C = 250\mu\text{A}$ , $V_{CE} = V_{GE}$	3.5		5.5 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 125^\circ\text{C}$			25 $\mu\text{A}$ 1.5 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 60A$ , $V_{GE} = 15V$ , Note 1 $T_J = 125^\circ\text{C}$		2.3 2.9	2.7 V V

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 60\text{A}, V_{CE} = 10\text{V}$ , Note 1	23	38	S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		4550	pF
$C_{oes}$			243	pF
$C_{res}$			77	pF
$Q_{g(on)}$	$I_C = 80\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		145	nC
$Q_{ge}$			42	nC
$Q_{gc}$			65	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 80\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 2\Omega$ Note 2		34	ns
$t_{ri}$			103	ns
$E_{on}$			4.3	mJ
$t_{d(off)}$			90	ns
$t_{fi}$			86	ns
$E_{off}$			1.9	2.7 mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 150^\circ\text{C}</math></b> $I_C = 80\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 2\Omega$ Note 2		34	ns
$t_{ri}$			100	ns
$E_{on}$			5.7	mJ
$t_{d(off)}$			103	ns
$t_{fi}$			98	ns
$E_{off}$			2.5	mJ
$R_{thJC}$			0.25	$^\circ\text{C/W}$
$R_{thCS}$		0.05		$^\circ\text{C/W}$

### SOT-227B miniBLOC (IXYN)



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

### Reverse Sonic Diode (FRD)

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_F$	$I_F = 60\text{A}, V_{GE} = 0\text{V}$ , Note 1 $T_J = 125^\circ\text{C}$		1.9	2.7 V
$I_{RM}$	$I_F = 60\text{A}, V_{GE} = 0\text{V}, T_J = 125^\circ\text{C}$ $-di_F/dt = 700\text{A}/\mu\text{s}, V_R = 600\text{V}$		41	A
$t_{rr}$			420	ns
$R_{thJC}$				0.42 $^\circ\text{C/W}$

#### Notes:

1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Switching times & energy losses may increase for higher  $V_{CE}$  (clamp),  $T_J$  or  $R_G$ .

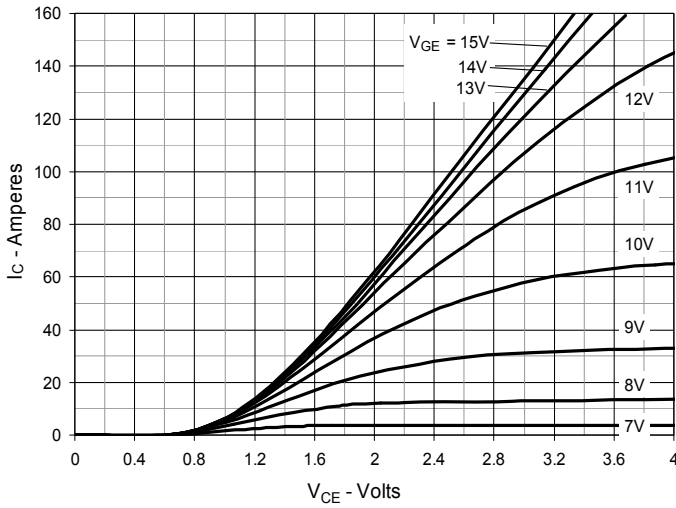
### PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

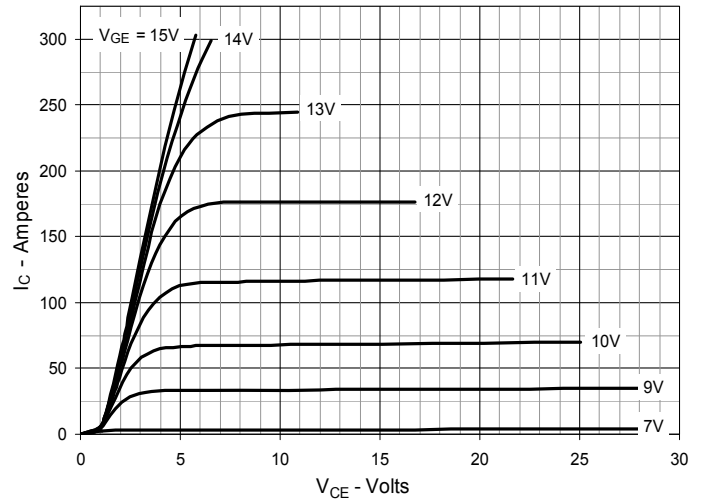
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2  
by one or more of the following U.S. patents: 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2  
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

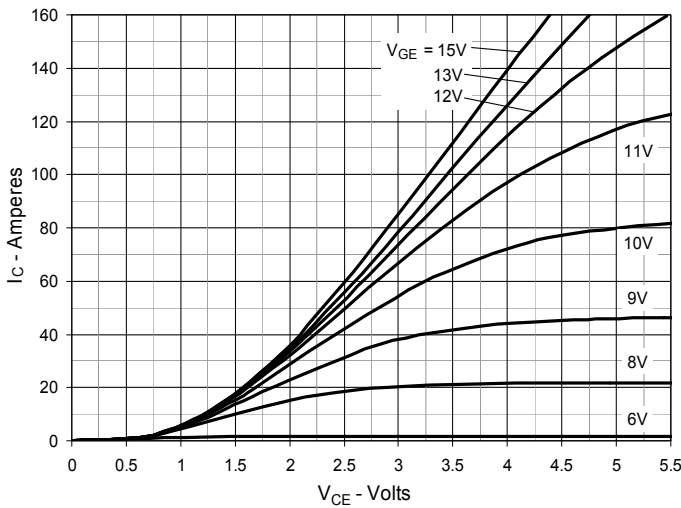
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



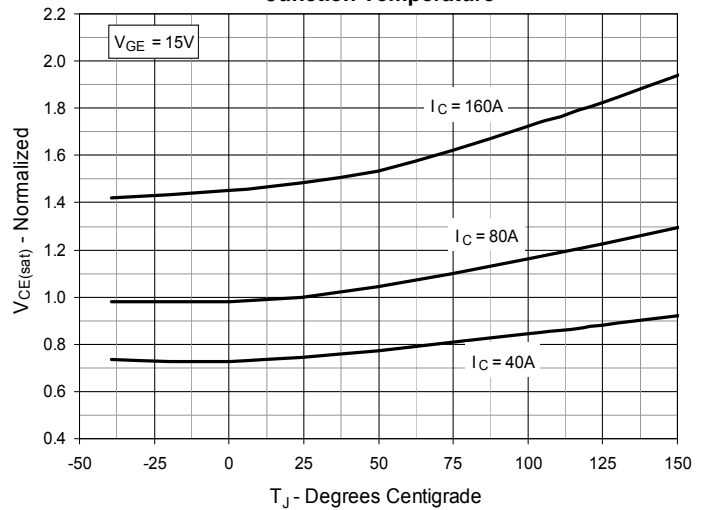
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



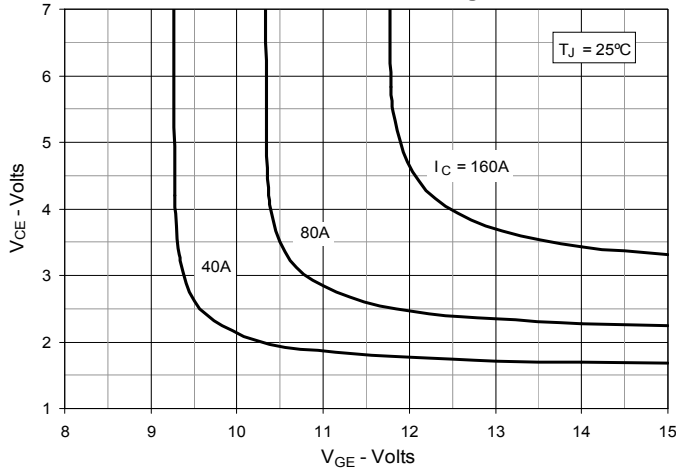
**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$**



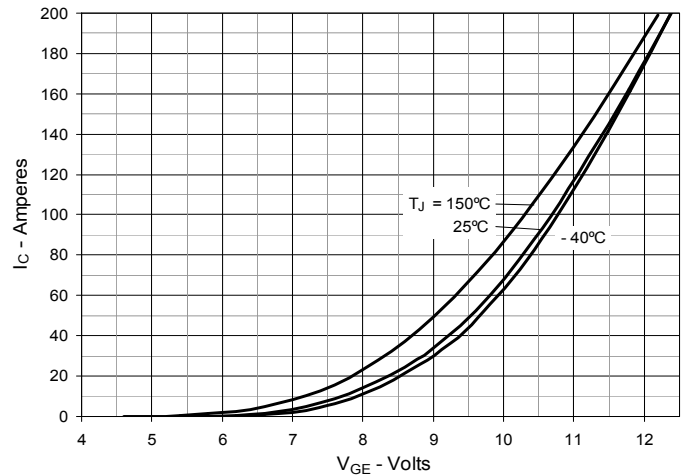
**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**



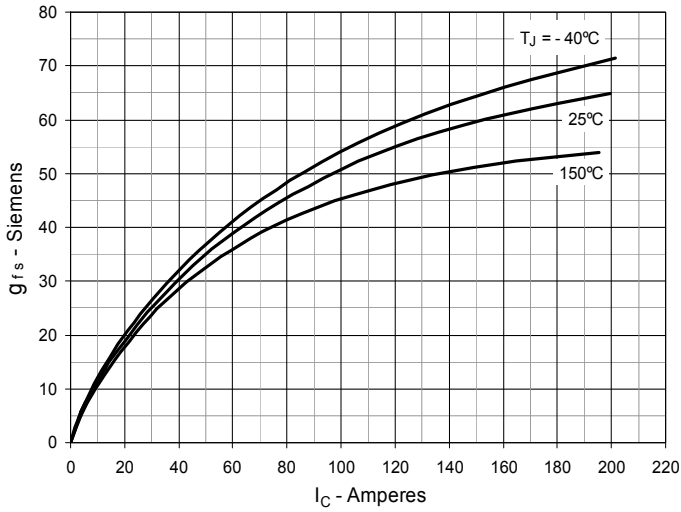
**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**



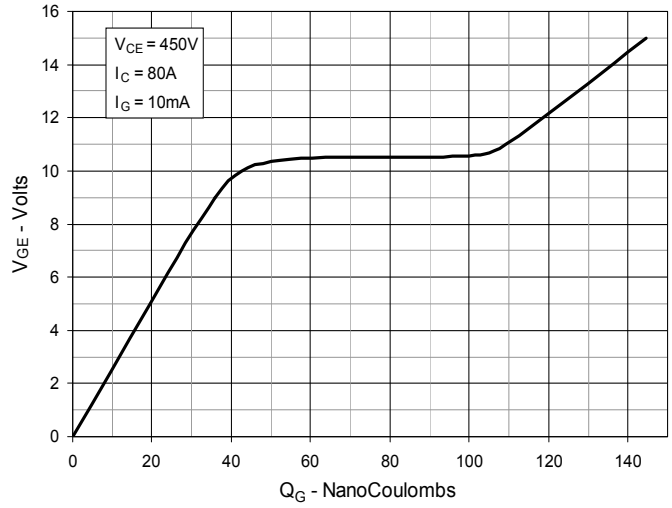
**Fig. 6. Input Admittance**



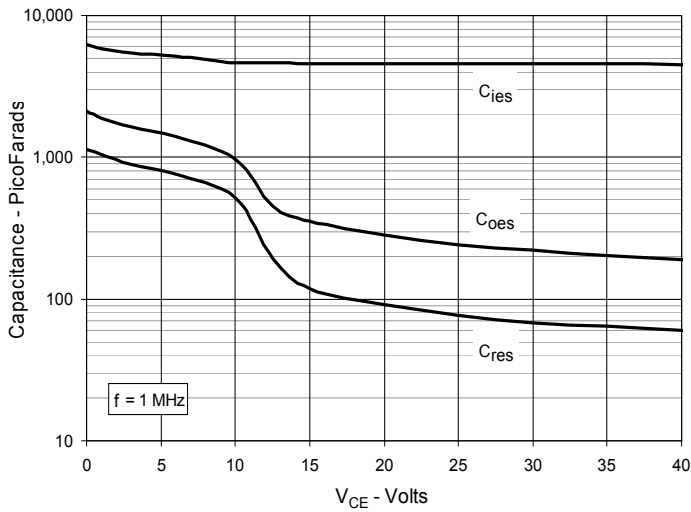
**Fig. 7. Transconductance**



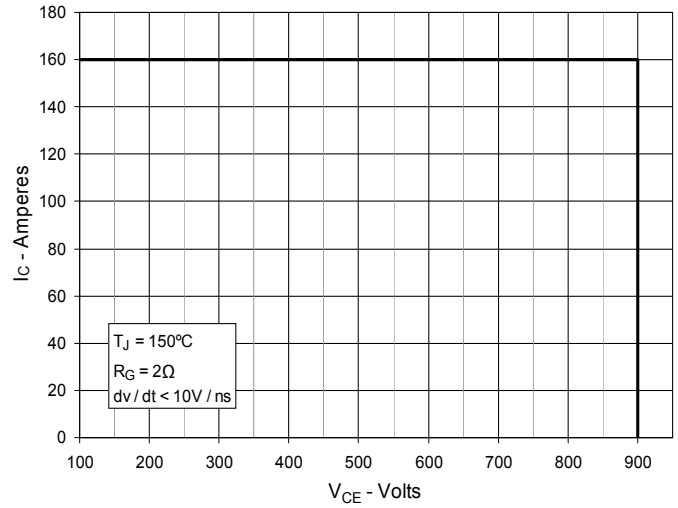
**Fig. 8. Gate Charge**



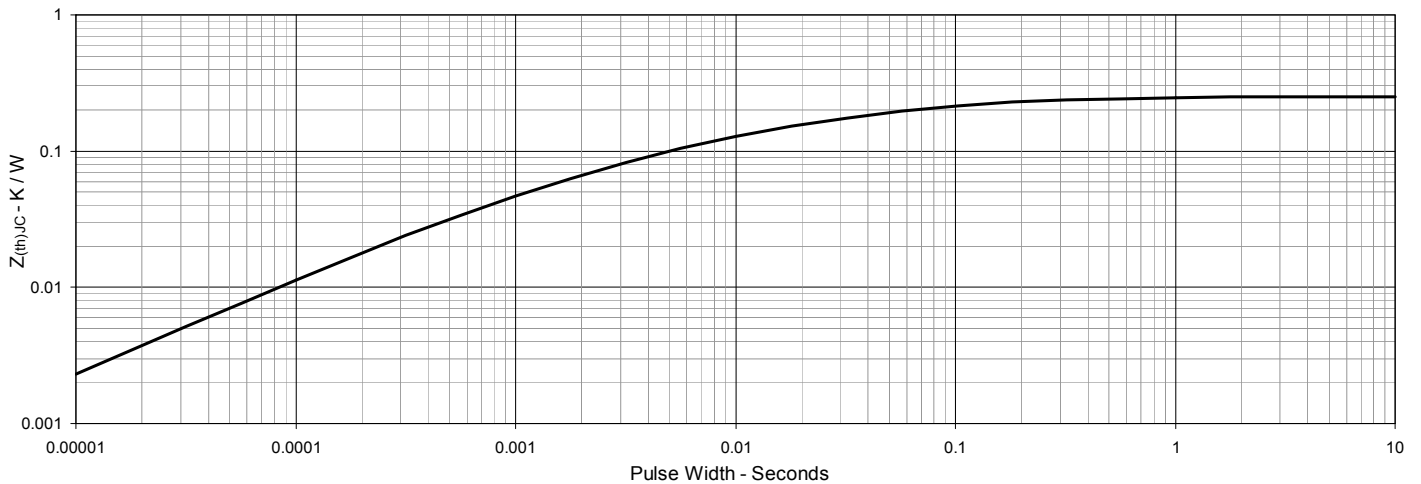
**Fig. 9. Capacitance**



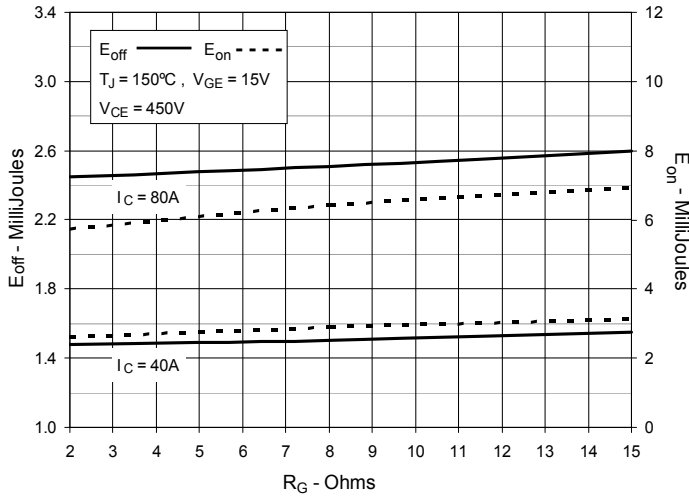
**Fig. 10. Reverse-Bias Safe Operating Area**



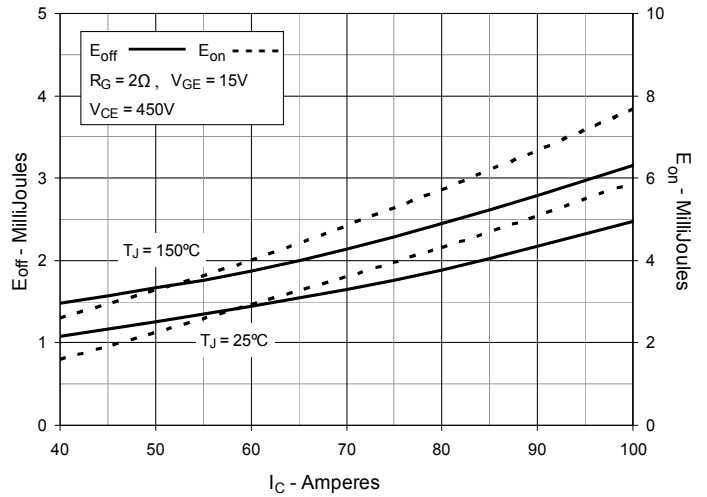
**Fig. 11. Maximum Transient Thermal Impedance**



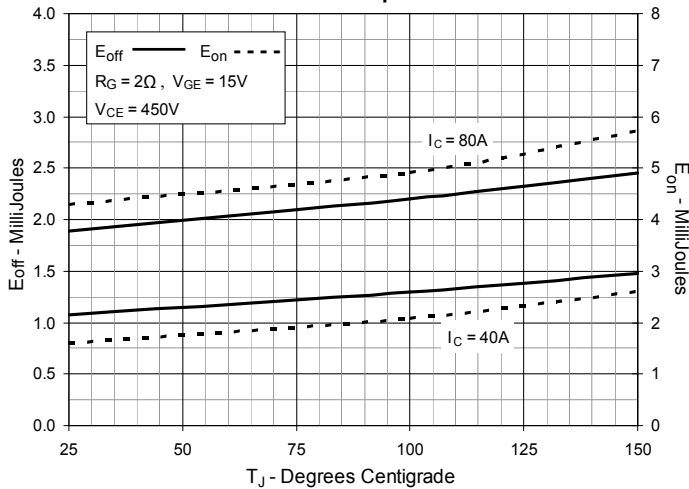
**Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance**



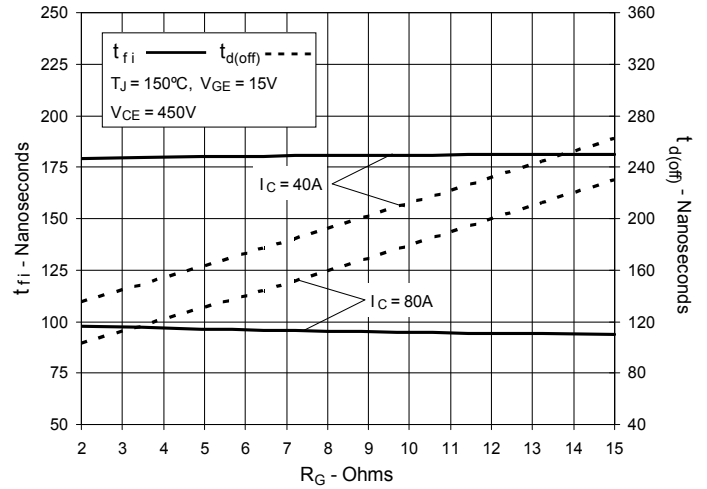
**Fig. 13. Inductive Switching Energy Loss vs. Collector Current**



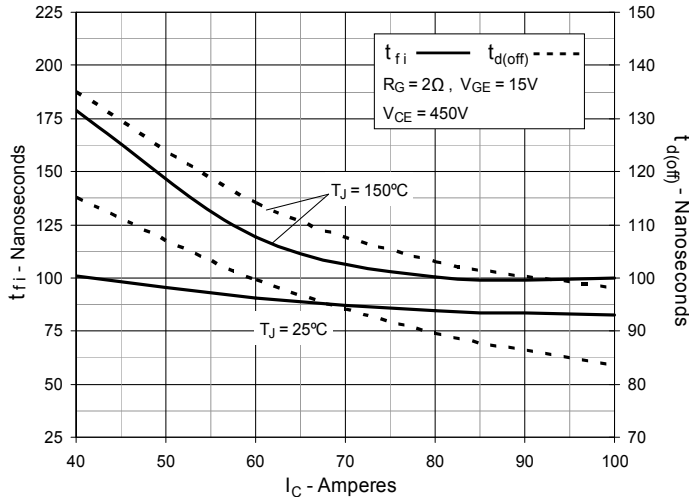
**Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature**



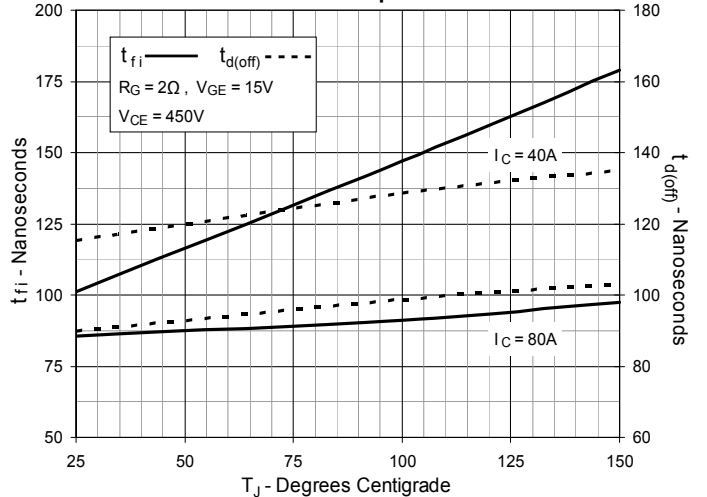
**Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance**



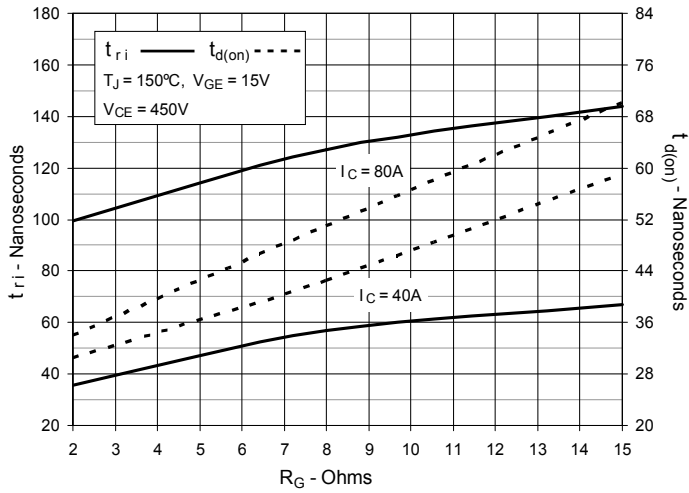
**Fig. 16. Inductive Turn-off Switching Times vs. Collector Current**



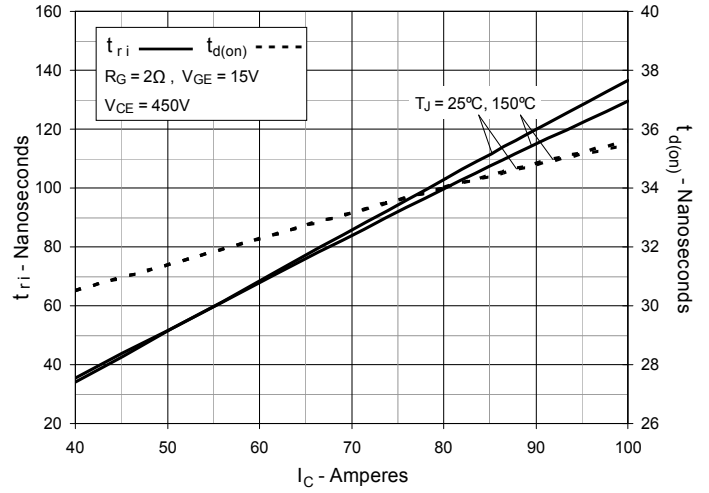
**Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature**



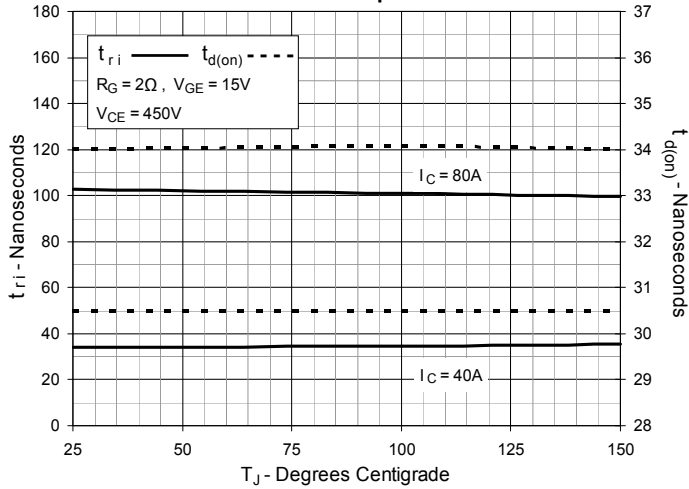
**Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance**

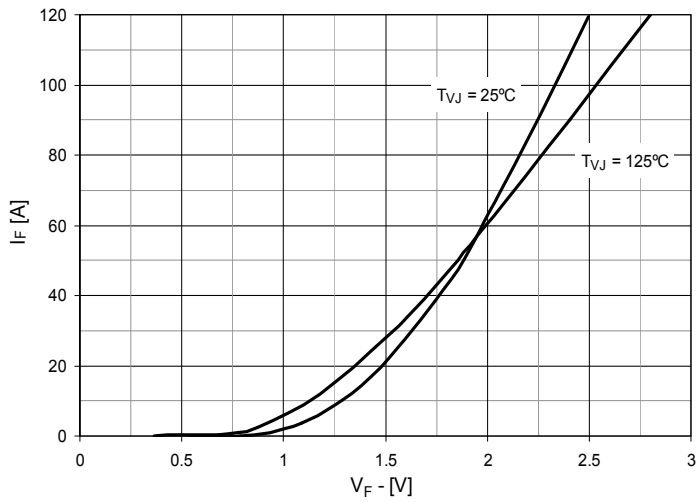
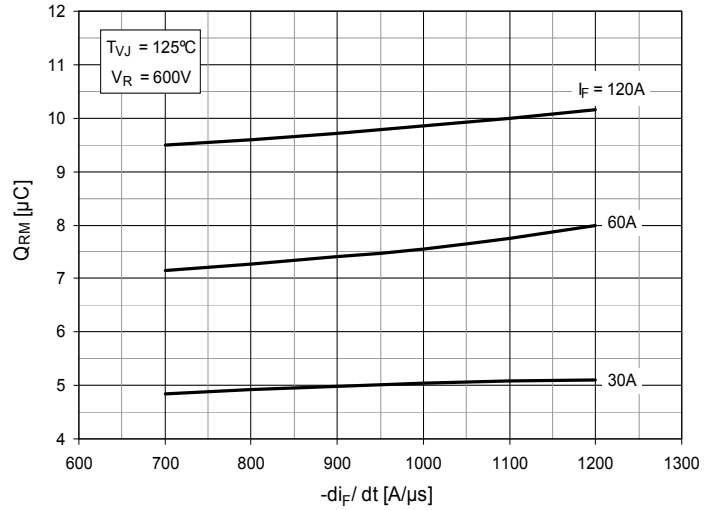
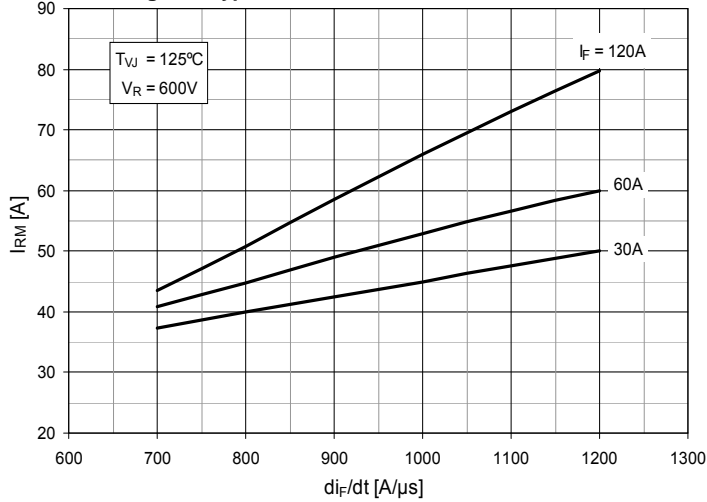
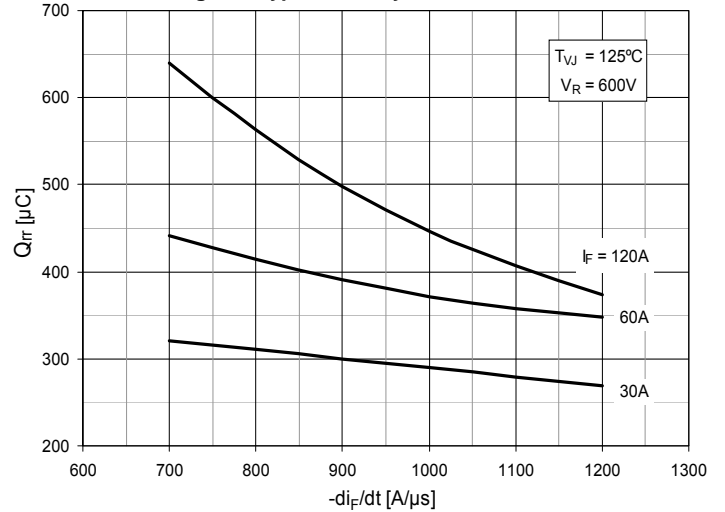
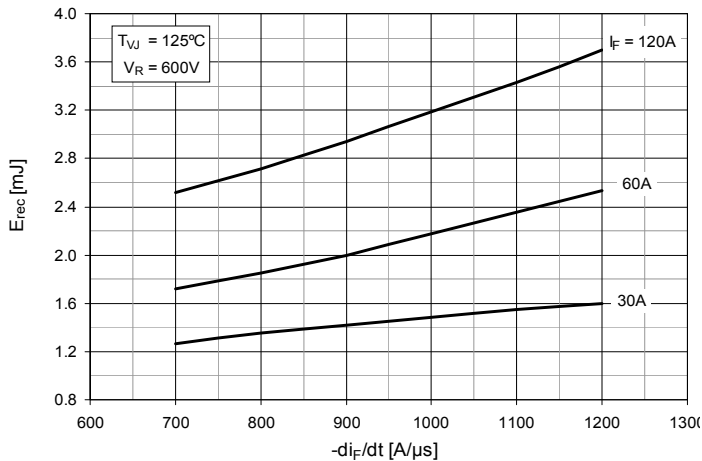
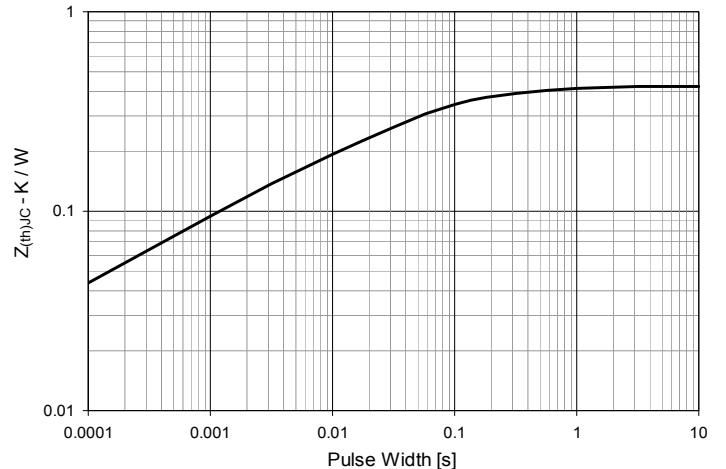


**Fig. 19. Inductive Turn-on Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature**



**Fig. 21. Typ. Forward characteristics**

**Fig. 22. Typ. Reverse Recovery Charge  $Q_{rr}$  vs.  $-di_F/dt$** 

**Fig. 23. Typ. Peak Reverse Current  $I_{RM}$  vs.  $-di_F/dt$** 

**Fig. 24. Typ. Recovery Time  $t_{rr}$  vs.  $-di_F/dt$** 

**Fig. 25. Typ. Recovery Energy  $E_{rec}$  vs.  $-di_F/dt$** 

**Fig. 26. Maximum Transient Thermal Impedance ( Diode )**




---

Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).